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## PEMB13; PUMB13

# PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

Rev. 4 — 7 December 2011

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	<b>3</b> -			NPN/NPN	Package
	NXP JEITA			complement	configuration
PEMB13	SOT666	-	PEMD13	PEMH13	ultra small and flat lead
PUMB13	SOT363	SC-88	PUMD13	PUMH13	very small

#### 1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	or					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8	10	12	



## 2. Pinning information

Table 3. Pinning

Tubic 0.	i iiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	[6] [5] [4]	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa212

## 3. Ordering information

Table 4. Ordering information

Type number	Package	Package			
	Name	Description	Version		
PEMB13	-	plastic surface-mounted package; 6 leads	SOT666		
PUMB13	SC-88	plastic surface-mounted package; 6 leads	SOT363		

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PEMB13	45
PUMB13	B*5

[1] \* = placeholder for manufacturing site code

## 5. Limiting values

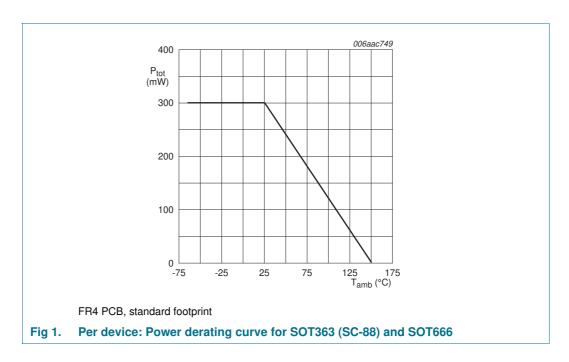
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V
$V_{EBO}$	emitter-base voltage	open collector	-	<b>-</b> 5	V
$V_{I}$	input voltage				
	positive		-	+5	V
	negative		-	-30	V
Io	output current		-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMB13 (SOT666)		[1][2] _	200	mW
	PUMB13 (SOT363)		<u>[1]</u> -	200	mW
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$			
	PEMB13 (SOT666)		[1][2] _	300	mW
	PUMB13 (SOT363)		<u>[1]</u> -	300	mW
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



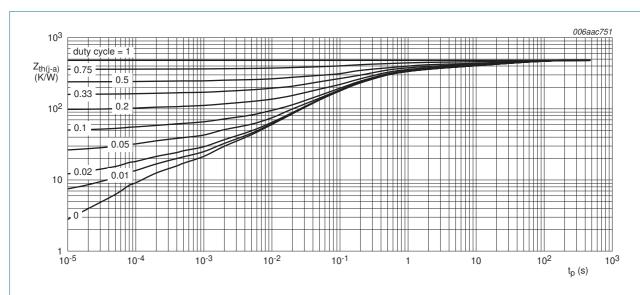
## 6. Thermal characteristics

Table 7. Thermal characteristics

Parameter	Conditions	Min	Тур	Max	Unit
or					
thermal resistance from junction to ambient	in free air				
PEMB13 (SOT666)		[1][2] _	-	625	K/W
PUMB13 (SOT363)		<u>[1]</u> -	-	625	K/W
thermal resistance from junction to ambient	in free air				
PEMB13 (SOT666)		[1][2] _	-	417	K/W
PUMB13 (SOT363)		[1] -	-	417	K/W
	thermal resistance from junction to ambient PEMB13 (SOT666) PUMB13 (SOT363)  thermal resistance from junction to ambient PEMB13 (SOT666)	thermal resistance from in free air junction to ambient  PEMB13 (SOT666)  PUMB13 (SOT363)  thermal resistance from in free air junction to ambient  PEMB13 (SOT666)	thermal resistance from in free air junction to ambient  PEMB13 (SOT666)  PUMB13 (SOT363)  [1] -  thermal resistance from in free air junction to ambient  PEMB13 (SOT666)  [1][2] -	thermal resistance from in free air junction to ambient  PEMB13 (SOT666)  PUMB13 (SOT363)  III  thermal resistance from in free air junction to ambient  PEMB13 (SOT666)  IIII	thermal resistance from in free air junction to ambient  PEMB13 (SOT666)  PUMB13 (SOT363)  III 625  thermal resistance from in free air junction to ambient  PEMB13 (SOT666)  IIII 417

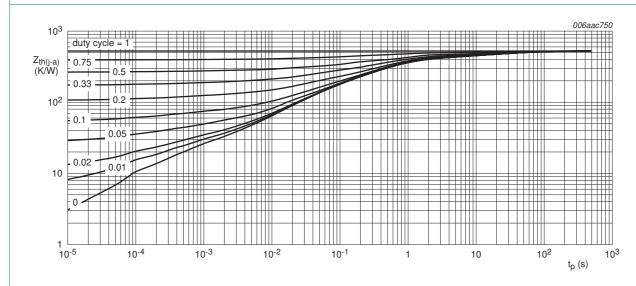
<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMB13 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB13 (SOT363); typical values

PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

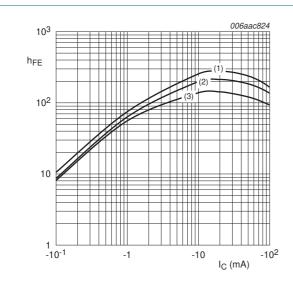
## 7. Characteristics

Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-170	μА
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE}$ = -5 V; $I_{C}$ = -100 $\mu A$	-	-0.6	-0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$	-1.3	-0.9	-	V
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8	10	12	
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; $ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

<sup>[1]</sup> Characteristics of built-in transistor



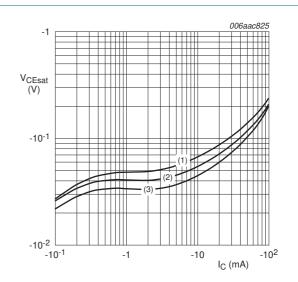
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 4. DC current gain as a function of collector current; typical values



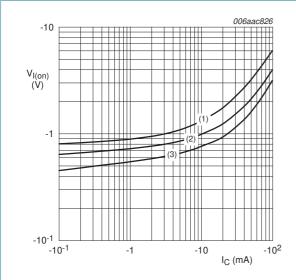
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



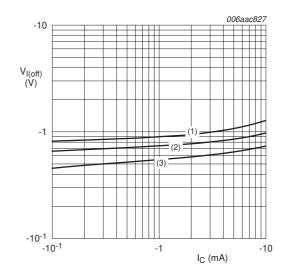
$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 6. On-state input voltage as a function of collector current; typical values



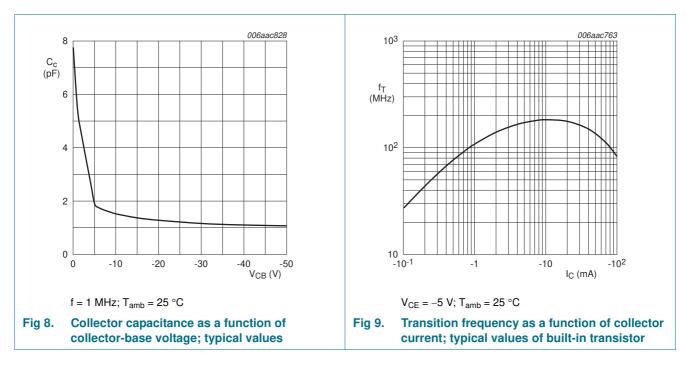
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 7. Off-state input voltage as a function of collector current; typical values

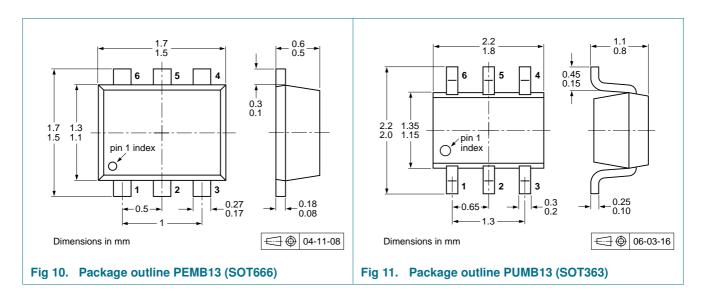


## 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 9. Package outline



PEMB13\_PUMB13

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## 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

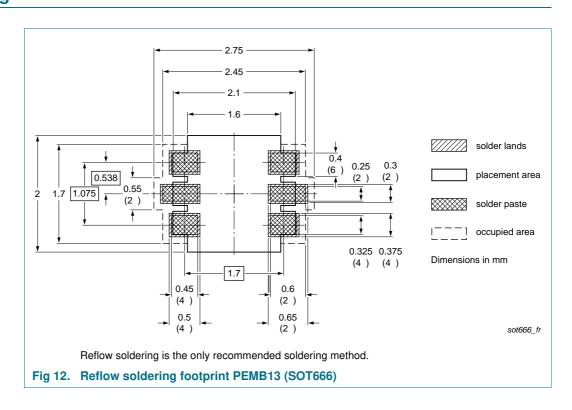
Туре	Package	Description		Packing quantity				
number			3000	4000	8000	10000		
PEMB13 SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-			
		4 mm pitch, 8 mm tape and reel	-	-115	-	-		
PUMB13	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135		
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165		

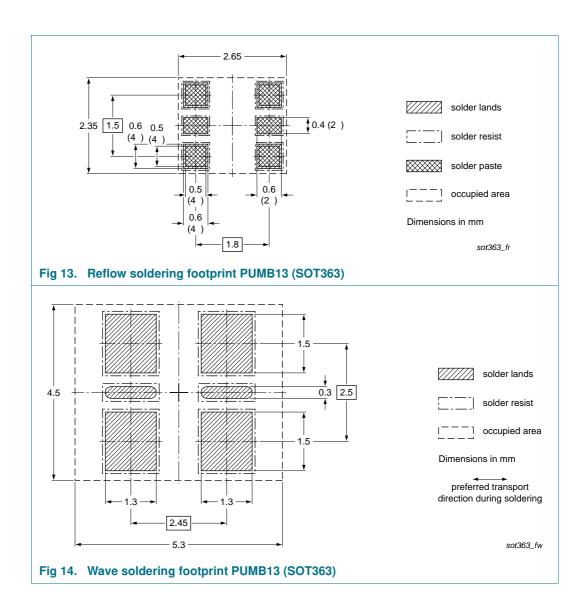
[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

## 11. Soldering





PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

## 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB13_PUMB13 v.4	20111207	Product data sheet	-	PEMB13_PUMB13 v.3
Modifications:	guidelines of  Legal texts h  Section 1 "Pr  Section 4 "M  Figure 1 to 9  Section 5 "Li  Section 6 "Tr  Table 8 "Cha V <sub>I(off)</sub> off-state  Section 8 "Te  Section 9 "Pr  Section 10 "F  Section 11 "S	of this document has been restricted in NXP Semiconductors. It is ave been adapted to the new roduct profile": updated arking": updated it is added it	ew company name whe lated d to V <sub>I(on)</sub> on-state inputed, f <sub>T</sub> added d by minimized package	th the new identity re appropriate.  voltage, V <sub>i(off)</sub> redefined to
PEMB13_PUMB13 v.3	20040415	Product data sheet	-	PEMB13_PUMB13 v.2
PEMB13_PUMB13 v.2	20031211	Product specification	-	PEMB13 v.1
PEMB13 v.1	20020114	Preliminary specification	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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PEMB13\_PUMB13

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PEMB13; PUMB13

PNP/PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 

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## PNP/PNP resistor-equipped transistors; R1 = 4.7 kΩ, R2 = 47 kΩ

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